

Description

The AU1271D3H is an uni-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The AU1271D3H complies with the IEC 61000-4-2 (ESD) with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into an ultra-small lead-free SOD-323 package. The small size and high ESD surge protection make AU1271D3H an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- Protects one data or power line
- Ultra low leakage: nA level
- Low clamping voltage
- 2-pin leadless package
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 83A (8/20 μs)
- RoHS Compliant

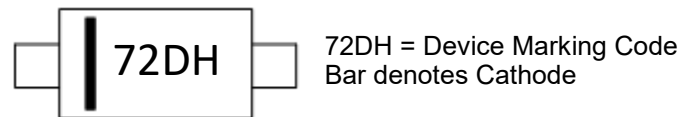
Mechanical Characteristics

- Package: SOD-323
- Case Material: “Green” Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

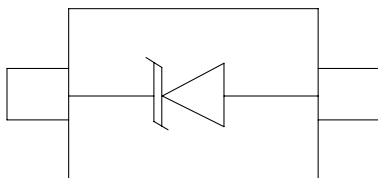
Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks, Desktops, Servers
- Portable Instrumentation
- Laser Diode Protection

Marking Information



Dimensions and Pin Configuration



SOD-323 (Top View)

Circuit and Pin Schematic

Ordering Information

Part Number	Packaging	Reel Size
AU1271D3H	3000/Tape & Reel	7 inch

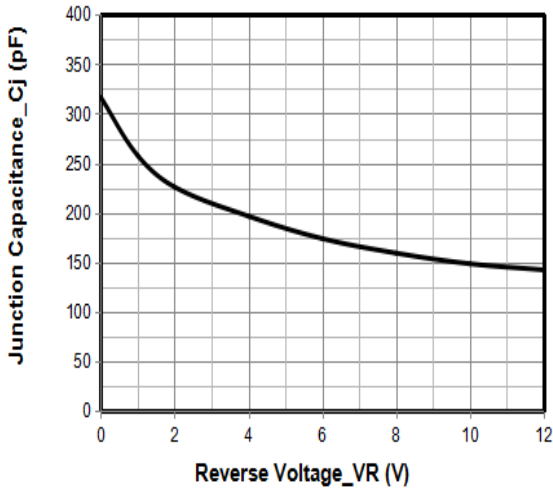
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	2075	W
Peak Pulse Current (8/20 μs)	Ipp	83	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	VESD	± 30 ± 30	kV
Operating Temperature Range	TJ	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^{\circ}\text{C}$

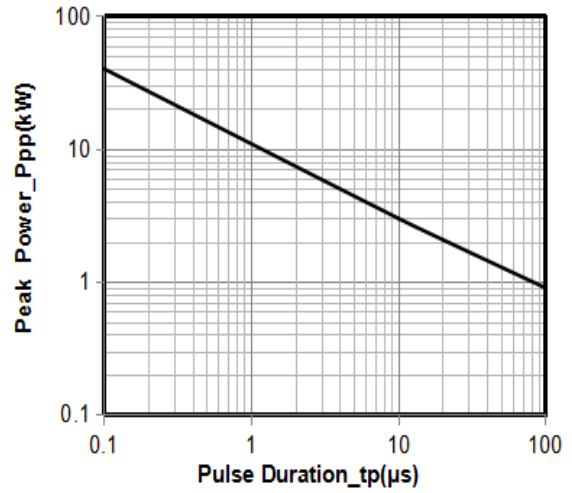
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			12	V	
Breakdown Voltage	VBR	13.3		17.8	V	IT = 1mA
Reverse Leakage Current	IR			0.2	μA	VRWM = 12V
Forward Voltage	VF		1.0	1.2	V	IF = 10mA
Clamping Voltage	VC			18	V	I _{PP} = 10A (8 x 20 μs pulse)
Clamping Voltage	VC			25	V	I _{PP} = 83A (8 x 20 μs pulse)
Junction Capacitance	CJ			400	pF	VR = 0V, f = 1MHz

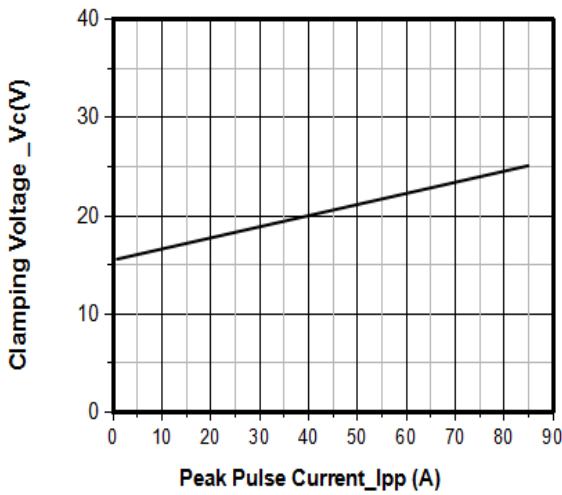
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



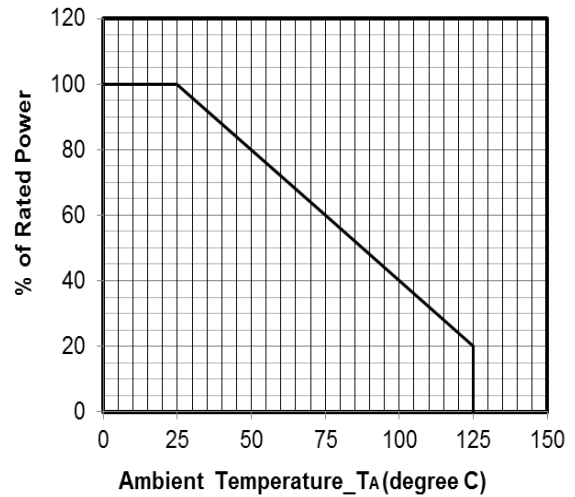
Junction Capacitance vs. Reverse Voltage



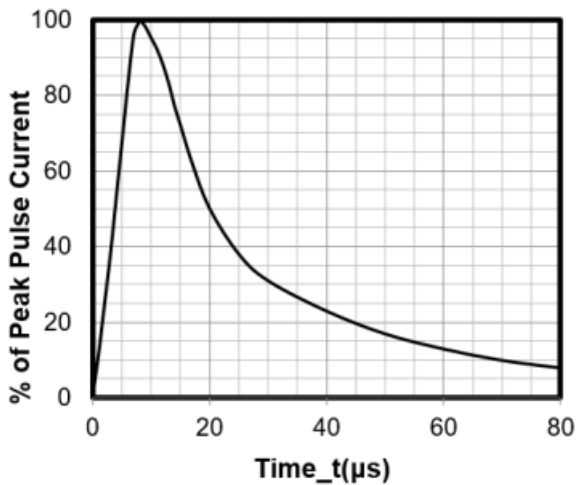
Peak Pulse Power vs. Pulse Time



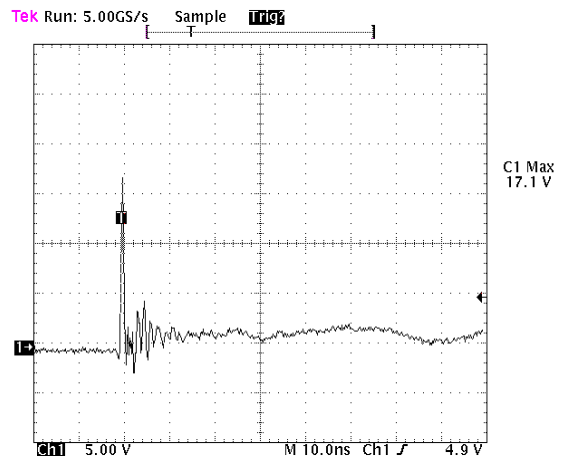
Clamping Voltage vs. Peak Pulse Current



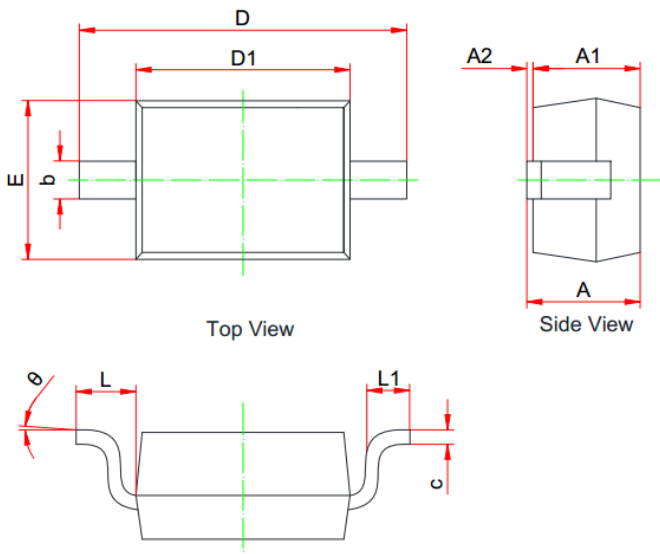
Power Derating Curve



8 X 20μs Pulse Waveform



**Note: Data is taken with a 10x attenuator
ESD Clamping Voltage
+8 kV Contact per IEC61000-4-2**

SOD-323 Package Outline Drawing


	MILLIMETERS		
	MIN	NOM	MAX
A	0.800	--	1.100
A1	0.800	--	0.900
A2	0.000	--	0.100
b	0.250	--	0.400
c	0.080	--	0.177
D1	1.600	1.700	1.800
D	2.300	--	2.800
E	1.150	--	1.400
L	0.475REF		
L1	0.100	--	0.500
Θ	0°	--	8°

Suggested Land Pattern

Unit: mm
Contact Information

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